

Patrick Berwian

List of Publications by Year in descending order

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papers

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times ranked

501
citing authors

#	ARTICLE	IF	CITATIONS
1	Fabrication and nanophotonic waveguide integration of silicon carbide colour centres with preserved spin-optical coherence. <i>Nature Materials</i> , 2022, 21, 67-73.	13.3	80
2	Lifetime limiting defects in 4H-SiC epitaxial layers: The influence of substrate originated defects. <i>Journal of Crystal Growth</i> , 2021, 560-561, 126033.	0.7	3
3	Deeper insight into lifetime-engineering in 4H-SiC by ion implantation. <i>Journal of Applied Physics</i> , 2019, 126, .	1.1	9
4	Minority Carrier Lifetime Measurements on 4H-SiC Epiwafers by Time-Resolved Photoluminescence and Microwave Detected Photoconductivity. <i>Materials Science Forum</i> , 2019, 963, 313-317.	0.3	0
5	Laser Writing of Scalable Single Color Centers in Silicon Carbide. <i>Nano Letters</i> , 2019, 19, 2377-2383.	4.5	70
6	Optical in-situ monitoring system for simultaneous measurement of thickness and curvature of thick layer stacks during hydride vapor phase epitaxy growth of GaN. <i>Journal of Crystal Growth</i> , 2015, 427, 99-103.	0.7	3
7	Thermal Simulation of Paralleled SiC PiN Diodes in a Module Designed for 6.5 kV/1 kA. <i>Materials Science Forum</i> , 2015, 821-823, 616-619.	0.3	1
8	Step-controlled homoepitaxial growth of 4H-SiC on vicinal substrates. <i>Journal of Crystal Growth</i> , 2013, 381, 127-133.	0.7	21
9	Experimental verification of the model by Klapper for 4H-SiC homoepitaxy on vicinal substrates. <i>Journal of Applied Physics</i> , 2013, 114, 183507.	1.1	9
10	Doping induced lattice misfit in 4H-SiC homoepitaxy. <i>Journal of Crystal Growth</i> , 2012, 349, 43-49.	0.7	11
11	Threading dislocations in n- and p-type 4H-SiC material analyzed by etching and synchrotron X-ray topography. <i>Journal of Crystal Growth</i> , 2011, 314, 21-29.	0.7	45
12	Selective etching of dislocations in GaN grown by low-pressure solution growth. <i>Journal of Crystal Growth</i> , 2010, 312, 3040-3045.	0.7	14
13	Vapor phase growth of GaN using GaN powder sources and thermogravimetric investigations of the evaporating behaviour of the source material. <i>Crystal Research and Technology</i> , 2008, 43, 14-21.	0.6	6
14	Low-pressure solution growth (LPSG) of GaN templates with diameters up to 3 inch. <i>Journal of Crystal Growth</i> , 2008, 310, 738-747.	0.7	22
15	On the influence of solution density on the formation of macroscopic defects in the liquid phase epitaxy of GaN. <i>Journal of Crystal Growth</i> , 2008, 311, 62-65.	0.7	8
16	Application of a thermogravimetric technique for the determination of low nitrogen solubilities in metals: Using iron as an example. <i>Thermochimica Acta</i> , 2008, 474, 36-40.	1.2	12
17	Crystal growth of compound semiconductors with low dislocation densities. , 2008, , .		1
18	Study on the kinetics of the formation reaction of GaN from Ga-solutions under ammonia atmosphere. <i>Journal of Crystal Growth</i> , 2007, 305, 326-334.	0.7	11

#	ARTICLE	IF	CITATIONS
19	Phase relations in the ternary Cu-Ga-In system. Thin Solid Films, 2007, 515, 5895-5898.	0.8	31
20	Kinetics of the reactive crystallization of CuInSe ₂ and CuGaSe ₂ chalcopyrite films for solar cell applications. Journal of Crystal Growth, 2006, 287, 408-413.	0.7	37
21	Considerations on facetting and on the atomic structure of the phase boundary in low-pressure solution growth of GaN. Journal of Crystal Growth, 2006, 297, 133-137.	0.7	8
22	In situ resistivity measurements of precursor reactions in the Cu-In-Ga system. Thin Solid Films, 2003, 431-432, 41-45.	0.8	11
23	Formation of CuInSe ₂ by the annealing of stacked elemental layers—analysis by in situ high-energy powder diffraction. Thin Solid Films, 2003, 437, 297-307.	0.8	86
24	Dislocation Conversion and Propagation during Homoepitaxial Growth of 4H-SiC. Materials Science Forum, 0, 645-648, 299-302.	0.3	11
25	4H-SiC Homoepitaxial Growth on Substrates with Different Off-Cut Directions. Materials Science Forum, 0, 679-680, 55-58.	0.3	6
26	Influence of Epilayer Thickness and Structural Defects on the Minority Carrier Lifetime in 4H-SiC. Materials Science Forum, 0, 740-742, 633-636.	0.3	5
27	SXRT Investigations on Electrically Stressed 4H-SiC PiN Diodes for 6.5 kV. Materials Science Forum, 0, 740-742, 899-902.	0.3	3
28	HCl Assisted Growth of Thick 4H-SiC Epilayers for Bipolar Devices. Materials Science Forum, 0, 778-780, 210-213.	0.3	1
29	Imaging Defect Luminescence of 4H-SiC by Ultraviolet-Photoluminescence. Solid State Phenomena, 0, 242, 484-489.	0.3	14
30	Modelling of Effective Minority Carrier Lifetime in 4H-SiC n-Type Epilayers. Materials Science Forum, 0, 858, 341-344.	0.3	2
31	Optical Stressing of 4H-SiC Material and Devices. Materials Science Forum, 0, 924, 196-199.	0.3	2
32	Influence and Mutual Interaction of Process Parameters on the $Z^{1/2}$ Defect Concentration during Epitaxy of 4H-SiC. Materials Science Forum, 0, 924, 112-115.	0.3	4
33	Influence of Substrate Properties on the Defectivity and Minority Carrier Lifetime in 4H-SiC Homoepitaxial Layers. Materials Science Forum, 0, 963, 109-113.	0.3	0